

## Aixtron SE

Ref. person: Michael Heuken

### Scientific publications:

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CMOS-compatible Ti/Al ohmic contacts ( $R_c < 0.3 \text{ } \Omega$ ) for u-AlGaN/AlN/GaN HEMTs by low temperature annealing ( $< 450 \text{ } ^\circ\text{C}$ )

(2014) Device Research Conference - Conference Digest, DRC, art. no. 6872304, pp. 75-76.

Slawinski, M., Brast, M., Zhang, X.D., Merget, F., Witzens, J., Heuken, M., Vescan, A., Kalisch, H.

Improved light outcoupling from OLED by non-wave-guiding anode designs

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